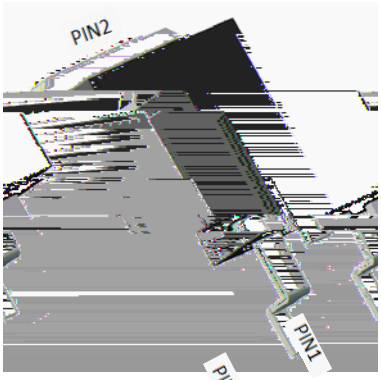
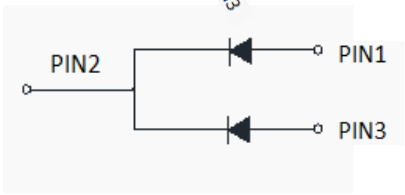
Schottky Diodes





Features

- ð High frequency operation
- ð Low forward voltage drop
- ð High purity， high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- ð Guard ring for enhanced ruggedness and long term reliability
- ð Meets MSL level 1， per J-STD-020， LF maximum peak of 260[
  Molding compound m
  rating， RoHS-compli
- ðTerminals: Tin plated leads， solderable per J-STD-002 and J ESD22-B102
- ðPolarity: As marked

yMaximum Ratings (Ta = 25Ņ Unless otherwise specified

PARAMETER	SYMBOL	UNIT	MBRBL30100CT
Device marking code			MBRBL30100CT
Repetitive Peak Reverse Voltage	V_{RRM}	V	100
Average Rectified Output Current @60Hz sine wave， R-load， TĮ= 25	I_O	A	30
Surge(Non-repetitive)Forward Current @60Hz half sine-wave， 1 cycle， TĮ= 25	I_{FSM}	A	200
Current Squared Time @1ms Ò t < 8.3ms T jĮ= 25	I^2t	A^2s	167
Storage Temperature	Tstg	Ņ	-55 ~ +150
Junction Temperature	T j	Ņ	-55 ~ +150

yElectrical Characteristics Ĉ Ta = 25Ņ Unless otherwise specified

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	MBRBL30100CT
Maximum instantaneous forward voltage drop per diode	V_{FM}	V	I_{FM} = 15.0A	0.72
Maximum DC reverse current at rated DC blocking voltage per diode	I_{RRM1}	mA	V_{RM} = V_{RRM} T_a = 25Ņ	0.1
	I_{RRM2}		V_{RM} = V_{RRM} T_a = 100Ņ	20

Note1:Pulse test:300uS pulse widh，1% duty cycle

Note2:Pulse test:pulse widh 40mS

Outline Dimensions

TO-263		
Dim	Min	Max
A	9.5	11.5
B	9.7	10.5
C	8.4	9.0
D		

Suggested Pad Layout